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November 2013

FDP20N50 / FDPF20N50 / FDPF20N50T

N-Channel UniFETTM MOSFET 500 V, 20 A, 230 m Ω

Features

- $R_{DS(on)}$ = 200 $m\Omega$ (Typ.) @ V_{GS} = 10 V, I_D = 10 A
- Low Gate Charge (Typ. 45.6 nC)
- Low C_{rss} (Typ. 27 pF)
- · 100% Avalanche Tested

Applications

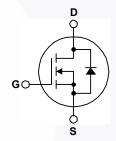
- LCD/LED/PDP TV
- Lighting
- · Uninterruptible Power Supply
- · AC-DC Power Supply

Description

UniFETTM MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.







Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FDP20N50	FDPF20N50 / FDPF20N50T	Unit
V_{DSS}	Drain-Source Voltage		500		
I _D	Drain Current - Continuous (T _C = 25°C) - Continuous (T _C = 100°C)		20 20 12.9 12.		A A
I _{DM}	Drain Current - Pulsed	(Note 1)	80	80 *	Α
V_{GSS}	Gate-Source voltage		±30		V
E _{AS}	Single Pulsed Avalanche Energy (Note 2)		1110		mJ
I _{AR}	Avalanche Current (Note 1)		20		Α
E _{AR}	Repetitive Avalanche Energy (Note 1)		25		mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		4.5		V/ns
P _D	Power Dissipation (T _C = 25°C) - Derate above 25°C	2	250 2.0	38.5 0.3	W/°C
T _{J,} T _{STG}	Operating and Storage Temperature Range		-55 to +150		°C
TL	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds		300		

^{*} Drain current limited by maximum junction temperature.

Thermal Characteristics

Symbol	Parameter	FDP20N50	FDPF20N50/ FDPF20N50T	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.5	3.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	62.5	C/VV

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDP20N50	FDP20N50	TO-220	Tube	N/A	N/A	50 units
FDPF20N50	FDPF20N50	TO-220F	Tube	N/A	N/A	50 units
FDPF20N50T	FDPF20N50	TO-220F	Tube	N/A	N/A	50 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Conditions		Тур.	Max.	Unit
Off Charac	Off Characteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$				V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C		0.5		V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 500 V, V _{GS} = 0 V V _{DS} = 400 V, T _C = 125°C			1 10	μ Α μ Α
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30 V, V _{DS} = 0 V			-100	nA
On Charac	teristics			•		
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	3.0		5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 10 A		0.20	0.23	Ω
9 _{FS}	Forward Transconductance	V _{DS} = 40 V, I _D = 10 A		24.6		S
Dynamic C	Characteristics				•	
C _{iss}	Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V,		2400	3120	pF
C _{oss}	Output Capacitance	f = 1.0 MHz		355	465	pF
C _{rss}	Reverse Transfer Capacitance			27		pF
Switching	Characteristics				•	
t _{d(on)}	Turn-On Delay Time	V _{DD} = 250 V, I _D = 20 A,		95	200	ns
t _r	Turn-On Rise Time	V_{GS} = 10 V, R_G = 25 Ω		375	760	ns
t _{d(off)}	Turn-Off Delay Time			100	210	ns
t _f	Turn-Off Fall Time	(Note 4)	/	105	220	ns
Q _g	Total Gate Charge	V _{DS} = 400 V, I _D = 20 A,		45.6	59.5	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 10 V	/	14.8		nC
Q _{gd}	Gate-Drain Charge	(Note 4)		21.6		nC
Drain-Sou	rce Diode Characteristics and Maximur	n Ratings				
I _S	Maximum Continuous Drain-Source Dio	de Forward Current			20	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				80	Α
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 20 A			1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 20 A,		507		ns
Q _{rr}	Reverse Recovery Charge	dI _F /dt =100 A/μs		7.20		μC

Notes

- 1. Repetitive rating: pulse-width limited by maximum junction temperature.
- 2. L = 5.0 mH, I $_{AS}$ = 20 A, V $_{DD}$ = 50 V, R $_{G}$ = 25 $\Omega,$ starting T $_{J}$ = 25 $^{\circ}C.$
- 3. I $_{SD}$ \leq 20 A, di/dt \leq 200 A/µs, V $_{DD}$ \leq BV $_{DSS}$, starting T $_{J}$ = 25°C.
- 4. Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

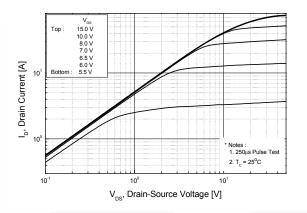


Figure 2. Transfer Characteristics

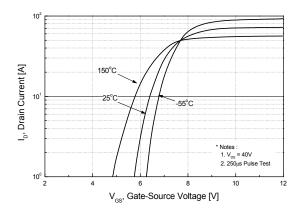


Figure 3. On-Resistance Variation vs.
Drain Current and Gate Voltage

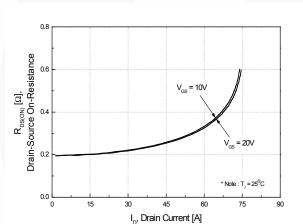


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperatue

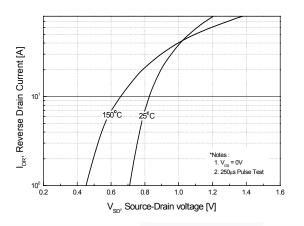


Figure 5. Capacitance Characteristics

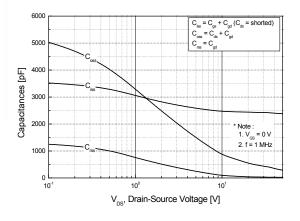
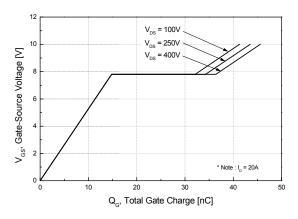


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

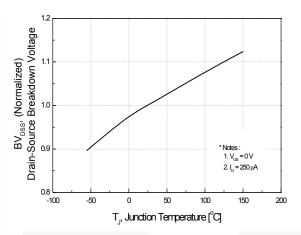


Figure 8. On-Resistance Variation vs. Temperature

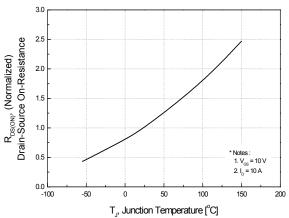
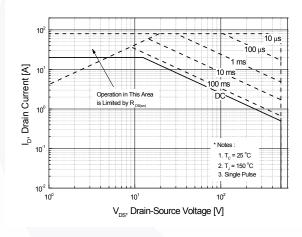


Figure 9-1. Maximum Safe Operating Area - FDP20N50

Figure 9-2. Maximum Safe Operating Area - FDPF20N50



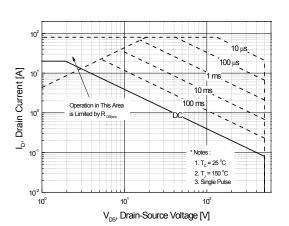
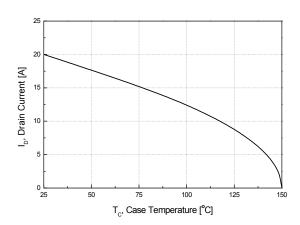


Figure 10. Maximum Drain Current vs. Case Temperature



Typical Performance Characteristics (Continued)

Figure 11-1. Transient Thermal Response Curve - FDP20N50

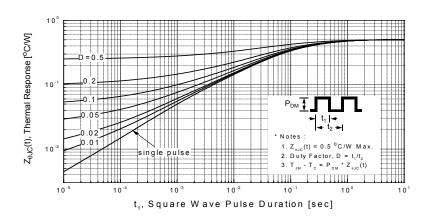
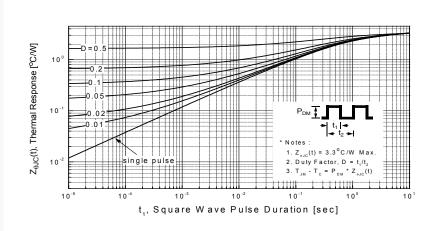


Figure 11-2. Transient Thermal Response Curve - FDPF20N50



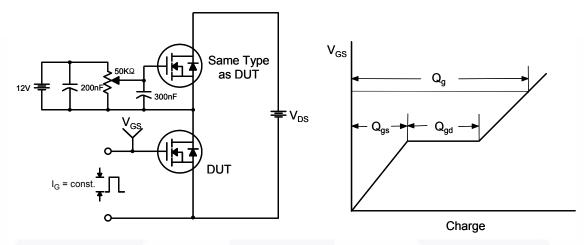


Figure 12. Gate Charge Test Circuit & Waveform

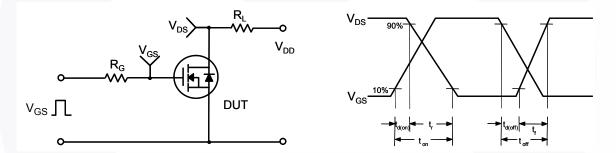


Figure 13. Resistive Switching Test Circuit & Waveforms

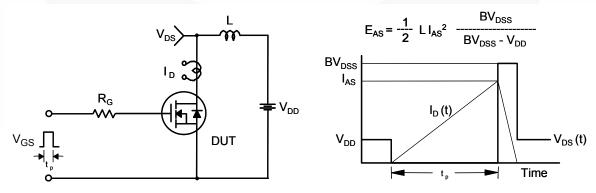


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

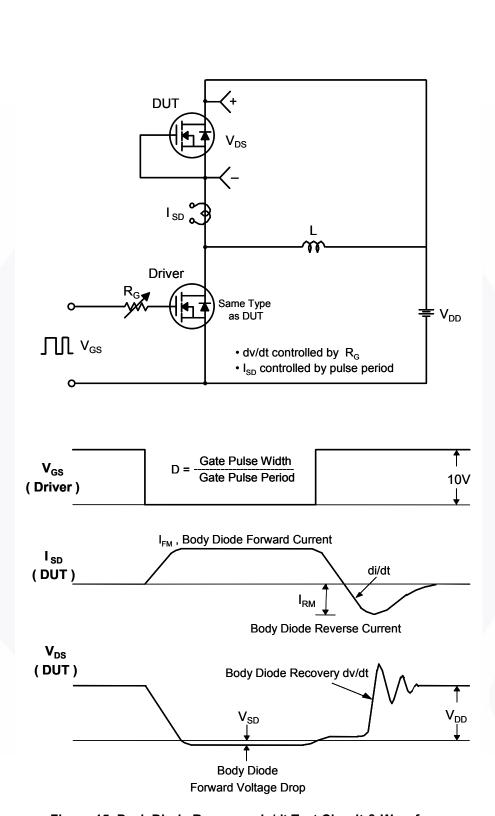


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions

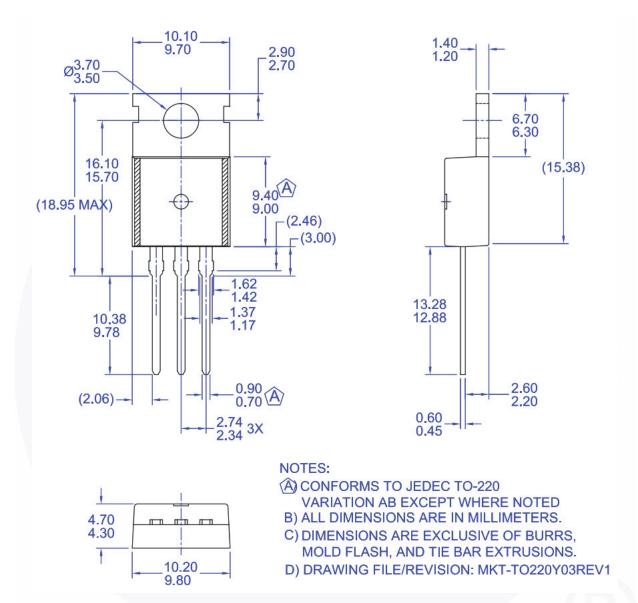


Figure 16. TO220, Molded, 3-Lead, Jedec Variation AB

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Mechanical Dimensions

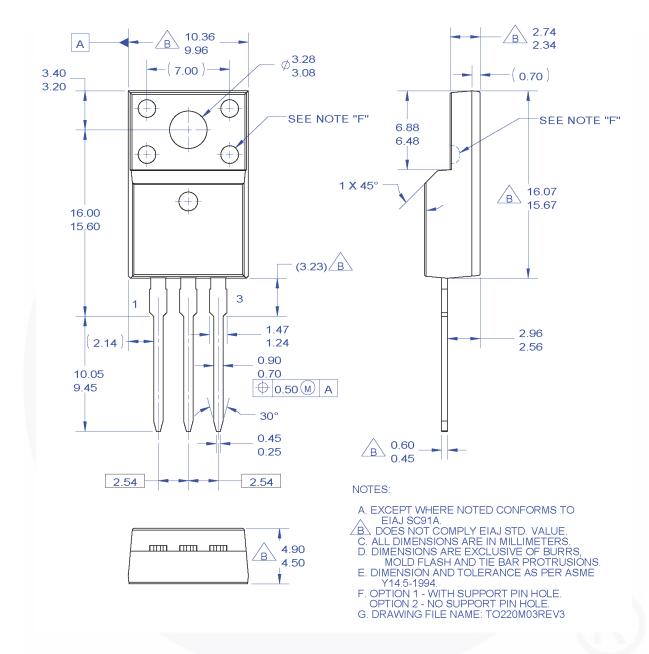


Figure 17. TO220, Molded, 3-Lead, Full Pack, EIAJ SC91, Straight Lead

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